

L Number	Hits	Search Text	DB	Time stamp
1	13	czochralski and (noble or inert or argon) near4 mbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 13:51
2	2	("6291874").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 14:11
3	2	("6299892").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 15:37
4	3	(zone-drawing or zone adj drawing) near12 czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 16:07
5	6	((("6291874") or ("4330361"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 16:07
-	1154	((257/620) or (438/906) or (437/83) or (437/84) or (117/19) or (117/84)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 11:43
-	1	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84"))).CCLS.) and (hydrogen with dop\$3 with silicon with wafer) same concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:09
-	90	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84"))).CCLS.) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:10
-	18	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84"))).CCLS.) and heat adj shield	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:11
-	37	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84"))).CCLS.) and nitrogen with dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:11
-	43	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84"))).CCLS.) and (argon with hydrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:12
-	201	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84"))).CCLS.) and oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:12
-	1	single adj silicon adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:14
-	54	silicon adj single adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:14

-	805	(117/13).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:17
-	0	((("117/13").CCLS.) and heat adj sjield.ti,ab. and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:17
-	5	((("117/13").CCLS.) and heat adj shield.ti,ab. and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:17
-	43	trench adj mosfet.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 20:15
-	9	(trench adj mosfet.ti.) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 20:15
-	4	"6191009"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/29 12:24
-	5	((("6191009") or ("6299982") or ("5942032") or ("6224668") or ("6197109")).PN.	USPAT	2002/01/29 12:25
-	5	((("6191009") or ("6299982") or ("5942032") or ("6244668") or ("6197109")).PN.	USPAT	2002/02/01 11:22
-	1	("6224668").PN.	USPAT	2002/02/01 11:29
-	4	("4210486").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 16:22
-	410	(liquid adj crystal adj display or lcd).ti. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 16:23
-	64	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar) (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 17:56
-	64	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar) (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 17:59
-	1	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:01
-	1	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:02
-	1	method.clm. and silicon.ti,ab. and wafer.clm. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:03

-	1	method.clm. and silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:03
-	1	silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:04
-	1	silicon and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:05
-	1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:06
-	1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:06
-	1	silicon and (h or hydrogen) and (pressure near5 mbar) and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:07
-	22	silicon and (h or hydrogen) and pressure and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 19:20
-	5	czochralski and pressure near3 mbar and oxygen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 19:21
-	23	czochralski.ti,ab. and pressure near3 argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:37
-	5	czochralski.ti,ab. and pressure near3 argon near3 mbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:37
-	0	czochralski.ti,ab. and pressure near3 argon near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:38
-	3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:38
-	3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:39
-	3	czochralski.ti,ab. and pressure near3 mbar near3 argon and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:39